INFRARED DIODE LASER AT 830nm

RN-III-830/1~2000mW

产品描述

It features ultra compact design, long lifetime, cost-effectiveness and easy operation. They are widely used in measurement, spectrum analysis, etc.

产品参数

RN-III-830/1~2000mW		
Central wavelength (nm)		830±10
Operating mode		CW
ASE Output power (mW)		>1, 100, 200, 300, …, 2000
Power stability (rms, over 4 hours)		<1%, <2%, <3% (<0.5%, optional)
Transverse mode		Multimode
Dimensions of beam at the aperture (mm)		~5×8
Beam divergence, full angle (mrad)		<2.5
Warm-up time (minutes)		<5
Beam height from base plate (mm)		24. 8
Operating temperature (℃)		10~35
Power supply	85-264VAC	PSU-III-LED/PSU-III-FDA (Frequency for 1Hz-30kHz)
	100-240VAC	PSU-A-D (Frequency for 30kHz -100kHz)
TTL / Analog modulation		TTL or Analog with 1Hz-1kHz 1kHz-10kHz, 10kHz-30kHz optional
Expected lifetime (hours)		10000
Warranty		1 year